a high-k layer deposited on the oxynitride layer~~, and~~

~~an electrode layer on the high-k layer~~.

25. (Original) The microstructure according to claim 24, wherein the thickness of the oxynitride layer is less than about 15 A.

26. (Original) The microstructure according to claim 24, wherein the thickness of the oxynitride layer is less than about 10 A.

27. (Canceled)

28. (Previously Presented) The microstructure according to claim 24, wherein the high-k layer comprises at least one of HfO_2, ZrO_2, Ta_2O_5, TiO_2, Al_2O_3, and HfSiO.

~~29.~~ 30. (Currently Amended) The microstructure according to claim ~~24~~ 46, wherein the electrode layer comprises at least one of W, Al, TaN, TaSiN, HfN, HfSiN, TiN, TiSiN, Re, Ru, and SiGe.

30. – 44. (Canceled)

45. (New) The method according to claim 1, further comprising:

depositing an electrode layer on the high-k layer.

~~46.~~ 28 (New) The microstructure according to claim 24, further comprising:

an electrode layer on the high-k layer.